

40V PNP SILICON LOW SATURATION TRANSISTOR IN SOT23

Features

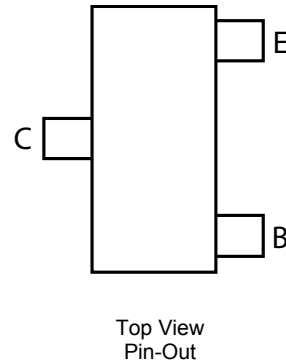
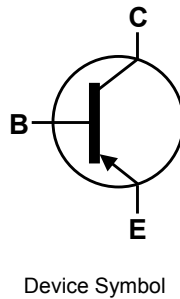
- $BV_{CEO} > -40V$
- $I_C = -1.5A$ Continuous Collector Current
- $I_{CM} = -4A$ Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < -220mV @ -1A$
- $R_{CE(SAT)} = 163m\Omega$ for a low equivalent on-resistance
- 625mW power dissipation
- h_{FE} characterised up to -3A for high current gain hold-up
- Complementary NPN Type: FMMT619
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP capable (Note 4)**

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 E3
- Weight 0.008 grams (approximate)

Applications

- Gate Driving MOSFETs and IGBTs
- DC-DC Converters
- Charging circuit
- Power switches

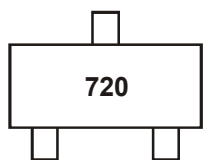


Ordering Information (Note 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT720TA	AEC-Q101	720	7	8	3,000
FMMT720QTA	Automotive	720	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
 5. For packaging details, go to our website at <http://www.diodes.com>

Marking Information



720 = Product Type Marking Code

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-1.5	A
Peak Pulse Current	I_{CM}	-4	A
Base Current	I_B	-500	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

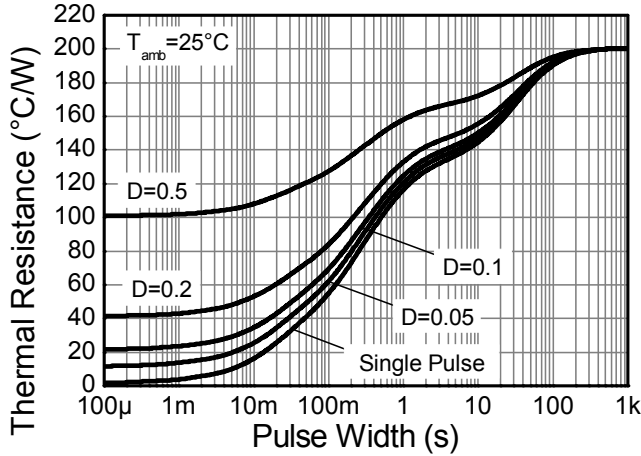
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_D	625	mW
Power Dissipation (Note 7)	P_D	806	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	155	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Leads (Note 8)	$R_{\theta JL}$	194	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 9)

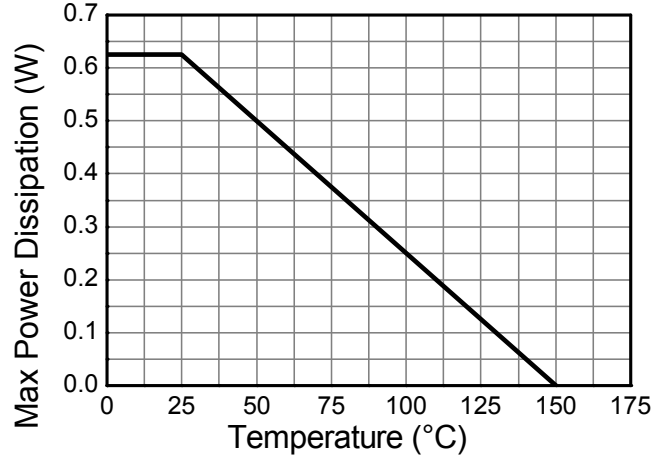
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
6. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 7. Same as note 6, except the device is measured at $t \leq 5$ sec.
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

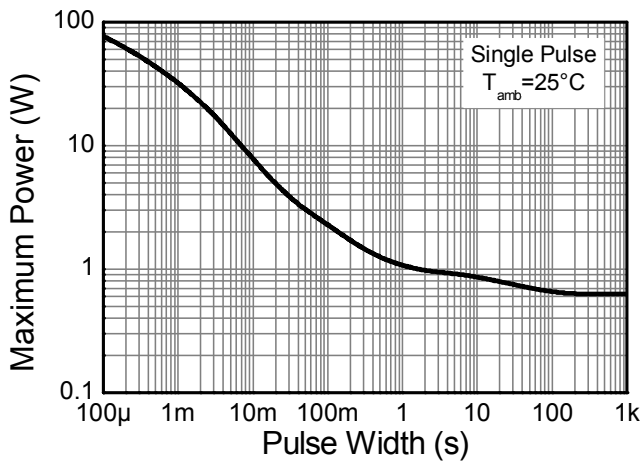
Thermal Characteristics and Derating information



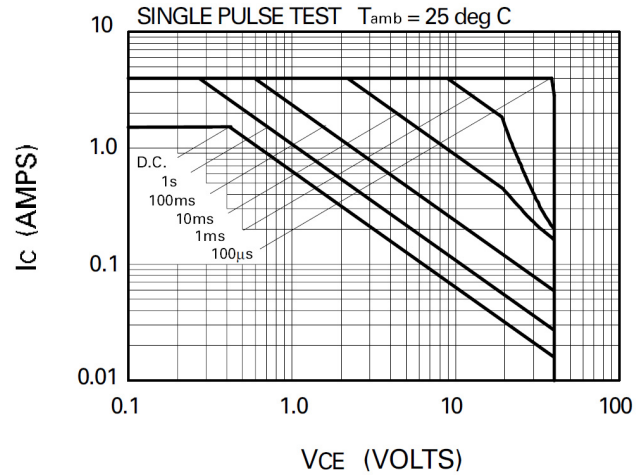
Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation



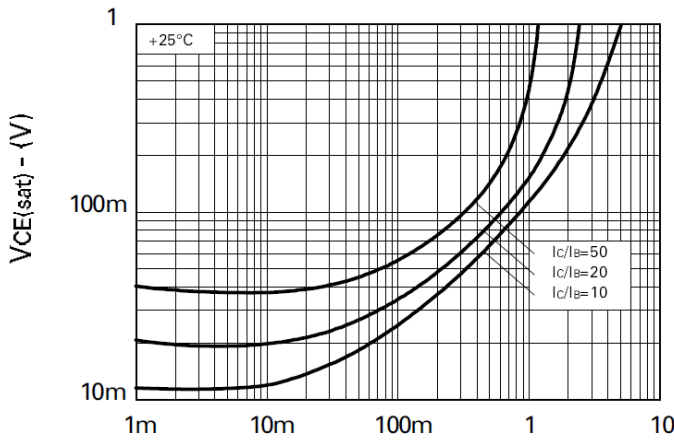
Safe Operating Area

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-40	-95	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-40	-85	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.8	-	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	-	<1	-100	nA	V _{CB} = -35V
Emitter Cutoff Current	I _{EBO}	-	<1	-100	nA	V _{EB} = -5.6V
Collector Emitter Cutoff Current	I _{CES}	-	<1	-100	nA	V _{CE} = -35V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	300	480	-	-	I _C = -10mA, V _{CE} = -2V
		300	450	-		I _C = -0.1A, V _{CE} = -2V
		180	290	-		I _C = -1A, V _{CE} = -2V
		60	130	-		I _C = -1.5A, V _{CE} = -2V
		12	22	-		I _C = -3A, V _{CE} = -2V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	-	-26	-40	mV	I _C = -0.1A, I _B = -10mA
		-	-150	-220	mV	I _C = -1A, I _B = -50mA
		-	-245	-330	mV	I _C = -1.5A, I _B = -100mA
Base-Emitter Turn-On Voltage(Note 10)	V _{BE(on)}	-	-0.80	-1.0	V	I _C = -1.5A, V _{CE} = -2V
Base-Emitter Saturation Voltage(Note 10)	V _{BE(sat)}	-	-0.89	-1.0	V	I _C = -1.5A, I _B = -75mA
Output Capacitance	C _{obo}	-	19	25	pF	V _{CB} = -10V, f = 1MHz
Transition Frequency	f _T	150	180	-	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Turn-On Time	t _{on}	-	40	-	ns	V _{CC} = -15V, I _C = -0.75A
Turn-Off Time	t _{off}	-	435	-	ns	I _{B1} = I _{B2} = -15mA

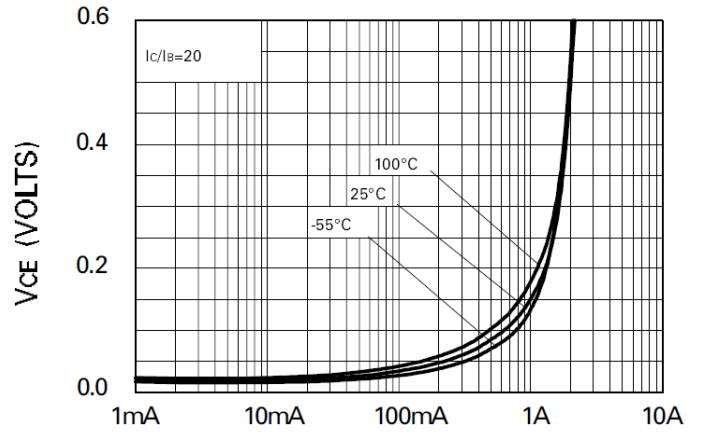
Notes: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



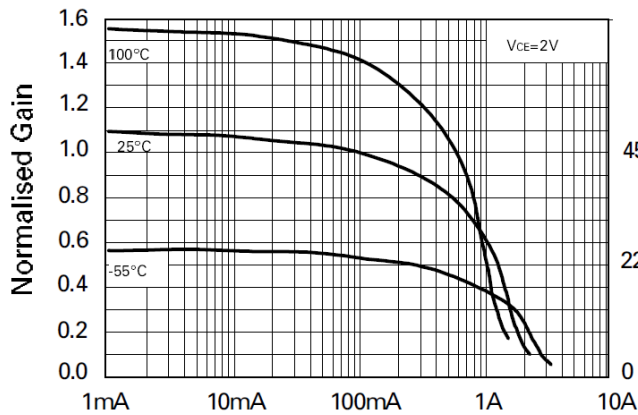
I_C - Collector Current (A)

$V_{CE(SAT)}$ v I_C



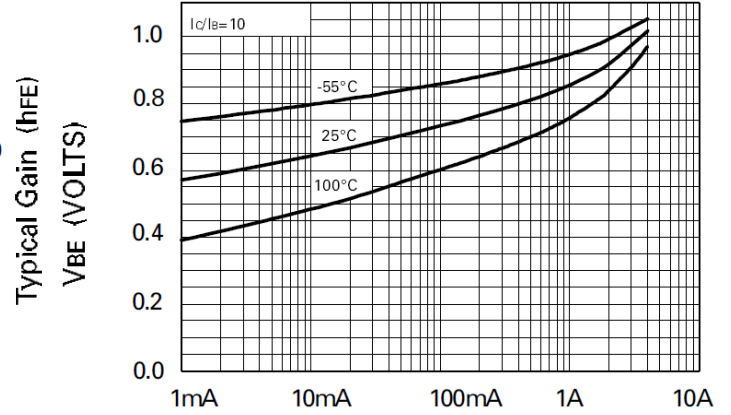
Collector Current

$V_{CE(SAT)}$ vs I_C



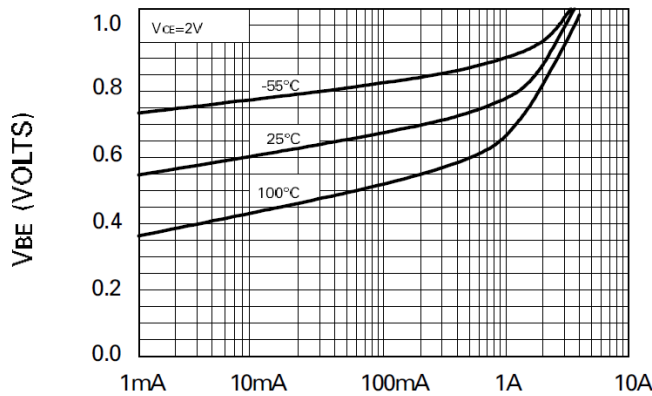
Collector Current

h_{FE} vs I_C



Collector Current

$V_{BE(SAT)}$ vs I_C

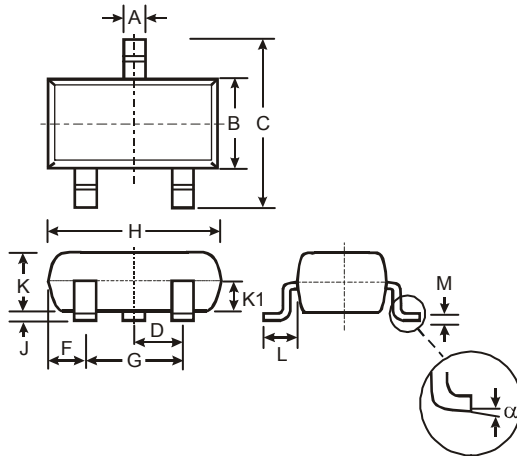


Collector Current

$V_{BE(ON)}$ vs I_C

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.

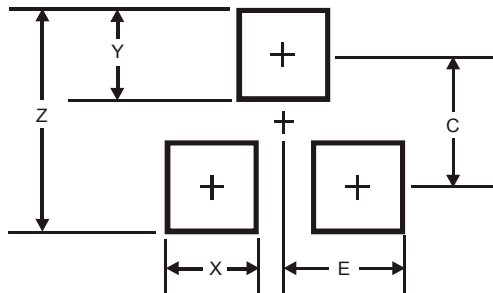


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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